

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-16. (Canceled)

17. (Currently Amended) A semiconductor device comprising a first semiconductor element using a crystalline semiconductor film as a first active region and a second semiconductor element using an amorphous semiconductor film as a second active region over an adhesive,

wherein the amorphous semiconductor film is located above the crystalline semiconductor film.

18. (Currently Amended) A semiconductor device comprising a first semiconductor element using a crystalline semiconductor film as a first active region and a second semiconductor element using an amorphous semiconductor film as a second active region over a plastic substrate,

wherein the amorphous semiconductor film is located above the crystalline semiconductor film.

19. (Currently Amended) A semiconductor device comprising a first semiconductor element using a crystalline semiconductor film as a first active region and a second semiconductor element using an amorphous semiconductor film as a second active region over an adhesive,

wherein the first semiconductor element and the second semiconductor element are electrically connected to each other, and

wherein the amorphous semiconductor film is located above the crystalline

semiconductor film.

20. (Currently Amended) A semiconductor device comprising a first semiconductor element using a crystalline semiconductor film as a first active region and a second semiconductor element using an amorphous semiconductor film as a second active region over a plastic substrate,

wherein the first semiconductor element and the second semiconductor element are electrically connected to each other, and

wherein the amorphous semiconductor film is located above the crystalline semiconductor film.

21. (Original) The semiconductor device according to Claim 17 or 19, wherein the adhesive is provided with exfoliate paper.

22. (Original) The semiconductor device according to any one of Claims 17 to 20, wherein the first semiconductor element is a thin film transistor.

23. (Original) The semiconductor device according to any one of Claims 17 to 20, wherein the second semiconductor element is a diode or a thin film transistor.

24. (Original) The semiconductor device according to any one of Claims 17 to 20, wherein the semiconductor device includes an optical sensor, a photoelectric conversion element, or a solar battery.

25. (New) A semiconductor device comprising:

a controller over a printed wiring board,

a power supply circuit over the printed wiring board,

an optical sensor over the printed wiring board comprising a first semiconductor

element using a crystalline semiconductor film as a first active region and a second semiconductor element using an amorphous semiconductor film as a second active region over a plastic substrate.

26. (New) The semiconductor device according to Claim 25, wherein the first semiconductor element is a thin film transistor.

27. (New) The semiconductor device according to Claim 25; wherein the second semiconductor element is a diode or a thin film transistor.

28. (New) The semiconductor device according to Claim 25, wherein the semiconductor device is a module of an electronic device.

29. (New) The semiconductor device according to Claim 25, wherein the semiconductor device provides with a panel having a pixel portion, a scanning line driver circuit, and a signal line driver circuit.

30. (New) The semiconductor device according to Claim 25, wherein the optical sensor is provided through an FPC.